The paragraph beginning at page 14, line 16, has been replaced with the following, rewritten paragraph:

A3

-- Next, in step of FIG. 9B, and SiN film is deposited on the GaAs substrate **61** by plasma CVD process such that the SiN film covers the WSi gate electrode **63**, and side wall insulation films **63A** and **63B** are formed on both lateral side walls of the gate electrode **63** as a result of anisotropic etching process applied of the SiN film such that the etching proceeds generally perpendicular to the principal surface of the substrate **61.** --

The paragraph beginning at page 14, line 25 has been replaced with the following, rewritten paragraph:

A4

-- In the step of FIG. 9B, a further ion implantation process of Si^+ is conducted under an acceleration voltage of 50keV with a dose of 5 x $10cm^{-2}$ while using WSi gate electrode **63** and the side wall insulation films **63A** and **63B** as a self-aligned mask, and n^+-type diffusion regions **61D** and **61E** are formed in the GaAs substrate **61** at outer sides of the LDD regions **61B** and **61C,** respectively. --

IN THE CLAIMS:

Please amend Claim 1, as follows:

A5

1. (Amended) A semiconductor triode, comprising:

a compound semiconductor layer including a channel layer;

a first ohmic electrode supplying carriers into said channel layer;

a second ohmic electrode collecting carriers from said channel layer; and